74LVC1G66

Bilateral switch

Rev. 8 — 2 December 2011 | Product data sheet

1. General description

The 74LVC1G66 provides one single pole, single-throw analog switch function. It has two input/output terminals (Y and Z) and an active HIGH enable input pin (E). When E is LOW, the analog switch is turned off.

Schmitt-trigger action at the enable input makes the circuit tolerant of slower input rise and fall times across the entire V_{CC} range from 1.65 V to 5.5 V.

2. Features and benefits

- Wide supply voltage range from 1.65 V to 5.5 V
- Very low ON resistance:
  - 7.5 Ω (typical) at V_{CC} = 2.7 V
  - 6.5 Ω (typical) at V_{CC} = 3.3 V
  - 6 Ω (typical) at V_{CC} = 5 V
- Switch current capability of 32 mA
- High noise immunity
- CMOS low power consumption
- TTL interface compatibility at 3.3 V
- Latch-up performance meets requirements of JESD78 Class I
- ESD protection:
  - HBM JESD22-A114F exceeds 2000 V
  - MM JESD22-A115-A exceeds 200 V
- Enable input accepts voltages up to 5.5 V
- Multiple package options
- Specified from –40 °C to +85 °C and –40 °C to +125 °C

3. Ordering information

Table 1. Ordering information

Type number	Package			
	Temperature range	Name	Description	Version
74LVC1G66GW	–40 °C to +125 °C	TSSOP5	plastic thin shrink small outline package; 5 leads; body width 1.25 mm	SOT353-1
74LVC1G66GV	–40 °C to +125 °C	SC-74A	plastic surface-mounted package; 5 leads	SOT753
74LVC1G66GM	–40 °C to +125 °C	XSON6	plastic extremely thin small outline package; no leads; 6 terminals; body 1 × 1.45 × 0.5 mm	SOT886

Table 1. Ordering information *...continued*

Type number	Package			
	Temperature range	Name	Description	Version
74LVC1G66GF	–40 °C to +125 °C	XSON6	plastic extremely thin small outline package; no leads; 6 terminals; body 1 × 1 × 0.5 mm	SOT891
74LVC1G66GN	–40 °C to +125 °C	XSON6	extremely thin small outline package; no leads; 6 terminals; body 0.9 × 1.0 × 0.35 mm	SOT1115
74LVC1G66GS	–40 °C to +125 °C	XSON6	extremely thin small outline package; no leads; 6 terminals; body 1.0 × 1.0 × 0.35 mm	SOT1202

4. Marking

Table 2. Marking

Type number	Marking code[1]
74LVC1G66GW	VL
74LVC1G66GV	V66
74LVC1G66GM	VL
74LVC1G66GF	VL
74LVC1G66GN	VL
74LVC1G66GS	VL

[1] The pin 1 indicator is located on the lower left corner of the device, below the marking code.

5. Functional diagram

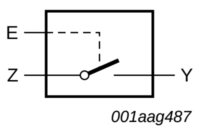


Fig 1. Logic symbol

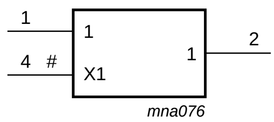


Fig 2. IEC logic symbol

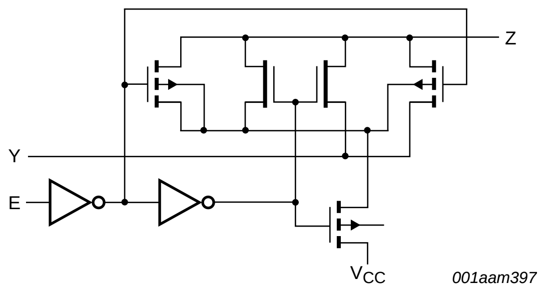


Fig 3. Logic diagram

6. Pinning information

6.1 Pinning

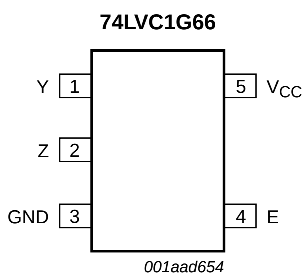


Fig 4. Pin configuration SOT353-1 and SOT753

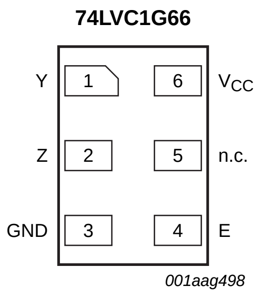


Fig 5. Pin configuration SOT886

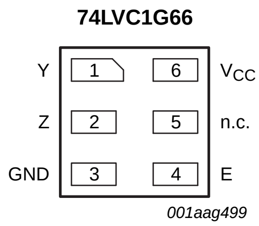


Fig 6. Pin configuration SOT891 and SOT1115 and SOT1202

6.2 Pin description

Table 3. Pin description

Symbol	Pin		Description
	SOT353-1, SOT753	SOT886, SOT891, SOT1115 and SOT1202	
Y	1	1	independent input or output
Z	2	2	independent output or input
GND	3	3	ground (0 V)
E	4	4	enable input (active HIGH)
n.c.	-	5	not connected
V_{CC}	5	6	supply voltage

7. Functional description

Table 4. Function table[1]

Input E	Switch
L	OFF-state
H	ON-state

[1] H = HIGH voltage level; L = LOW voltage level

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions		Min	Max	Unit
V_{CC}	supply voltage			–0.5	+6.5	V
V_I	input voltage		[1]	–0.5	+6.5	V
I_{IK}	input clamping current	$V_I < -0.5$ V or $V_I > V_{CC} + 0.5$ V		–50	-	mA
I_{SK}	switch clamping current	$V_I < -0.5$ V or $V_I > V_{CC} + 0.5$ V		-	±50	mA
V_{SW}	switch voltage	enable and disable mode	[2]	–0.5	V_{CC} + 0.5	V
I_{SW}	switch current	$V_{SW} > -0.5$ V or $V_{SW} < V_{CC} + 0.5$ V		-	±50	mA
I_{CC}	supply current			-	100	mA
I_{GND}	ground current			–100	-	mA
T_{stg}	storage temperature			–65	+150	°C
P_{tot}	total power dissipation	T_{amb} = –40 ° C to +125 °C	[3]	-	250	mW

[1] The minimum input voltage rating may be exceeded if the input current rating is observed.

[2] The minimum and maximum switch voltage ratings may be exceeded if the switch clamping current rating is observed.

[3] For TSSOP5 and SC-74A packages: above 87.5 °C the value of P_{tot} derates linearly with 4.0 mW/K.
For XSON6 packages: above 118 °C the value of P_{tot} derates linearly with 7.8 mW/K.

9. Recommended operating conditions

Table 6. Recommended operating conditions

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
V_{CC}	supply voltage			1.65	-	5.5	V
V_I	input voltage			0	-	5.5	V
V_{SW}	switch voltage		[1]	0	-	V_{CC}	V
T_{amb}	ambient temperature			–40	-	+125	°C
$\Delta t/\Delta V$	input transition rise and fall rate	V_{CC} = 1.65 V to 2.7 V	[2]	-	-	20	ns/V
		V_{CC} = 2.7 V to 5.5 V	[2]	-	-	10	ns/V

[1] To avoid sinking GND current from terminal Z when switch current flows in terminal Y, the voltage drop across the bidirectional switch must not exceed 0.4 V. If the switch current flows into terminal Z, no GND current will flow from terminal Y. In this case, there is no limit for the voltage drop across the switch.

[2] Applies to control signal levels.

10. Static characteristics

Table 7. Static characteristics

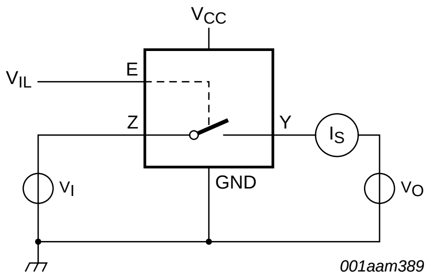
At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions		−40 °C to +85 °C			−40 °C to +125 °C		Unit
				Min	Typ[1]	Max	Min	Max	
V_{IH}	HIGH-level input voltage	V_{CC} = 1.65 V to 1.95 V		0.65V_{CC}	-	-	0.65V_{CC}	-	V
		V_{CC} = 2.3 V to 2.7 V		1.7	-	-	1.7	-	V
		V_{CC} = 2.7 V to 3.6 V		2.0	-	-	2.0	-	V
		V_{CC} = 4.5 V to 5.5 V		0.7V_{CC}	-	-	0.7V_{CC}	-	V
V_{IL}	LOW-level input voltage	V_{CC} = 1.65 V to 1.95 V		-	-	0.35V_{CC}	-	0.35V_{CC}	V
		V_{CC} = 2.3 V to 2.7 V		-	-	0.7	-	0.7	V
		V_{CC} = 2.7 V to 3.6 V		-	-	0.8	-	0.8	V
		V_{CC} = 4.5 V to 5.5 V		-	-	0.3V_{CC}	-	0.3V_{CC}	V
I_I	input leakage current	pin E; V_I = 5.5 V or GND; V_{CC} = 0 V to 5.5 V	[2]	-	±0.1	±5	-	±100	μA
$I_{S(OFF)}$	OFF-state leakage current	V_{CC} = 5.5 V; see Figure 7	[2]	-	±0.1	±5	-	±200	μA
$I_{S(ON)}$	ON-state leakage current	V_{CC} = 5.5 V; see Figure 8	[2]	-	±0.1	±5	-	±200	μA
I_{CC}	supply current	V_I = 5.5 V or GND; V_{SW} = GND or V_{CC}; V_{CC} = 1.65 V to 5.5 V	[2]	-	0.1	10	-	200	μA
ΔI_{CC}	additional supply current	pin E; V_I = V_{CC} − 0.6 V; V_{SW} = GND or V_{CC}; V_{CC} = 5.5 V	[2]	-	5	500	-	5000	μA
C_I	input capacitance			-	2.0	-	-	-	pF
$C_{S(OFF)}$	OFF-state capacitance			-	6.5	-	-	-	pF
$C_{S(ON)}$	ON-state capacitance			-	11	-	-	-	pF

[1] All typical values are measured at T_{amb} = 25 °C.

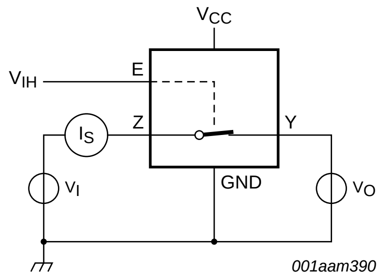
[2] These typical values are measured at V_{CC} = 3.3 V.

10.1 Test circuits



$V_I = V_{CC}$ or GND and V_O = GND or V_{CC}.

Fig 7. Test circuit for measuring OFF-state leakage current



$V_I = V_{CC}$ or GND and V_O = open circuit.

Fig 8. Test circuit for measuring ON-state leakage current

10.2 ON resistance

Table 8. ON resistance

At recommended operating conditions; voltages are referenced to GND (ground 0 V); for graphs see Figure 10 to Figure 15.

Symbol	Parameter	Conditions	–40 °C to +85 °C			–40 °C to +125 °C		Unit
			Min	Typ[1]	Max	Min	Max	
$R_{ON(peak)}$	ON resistance (peak)	V_I = GND to V_{CC}; see Figure 9						
		I_{SW} = 4 mA; V_{CC} = 1.65 V to 1.95 V	-	34.0	130	-	195	Ω
		I_{SW} = 8 mA; V_{CC} = 2.3 V to 2.7 V	-	12.0	30	-	45	Ω
		I_{SW} = 12 mA; V_{CC} = 2.7 V	-	10.4	25	-	38	Ω
		I_{SW} = 24 mA; V_{CC} = 3.0 V to 3.6 V	-	7.8	20	-	30	Ω
		I_{SW} = 32 mA; V_{CC} = 4.5 V to 5.5 V	-	6.2	15	-	23	Ω
$R_{ON(rail)}$	ON resistance (rail)	V_I = GND; see Figure 9						
		I_{SW} = 4 mA; V_{CC} = 1.65 V to 1.95 V	-	8.2	18	-	27	Ω
		I_{SW} = 8 mA; V_{CC} = 2.3 V to 2.7 V	-	7.1	16	-	24	Ω
		I_{SW} = 12 mA; V_{CC} = 2.7 V	-	6.9	14	-	21	Ω
		I_{SW} = 24 mA; V_{CC} = 3.0 V to 3.6 V	-	6.5	12	-	18	Ω
		I_{SW} = 32 mA; V_{CC} = 4.5 V to 5.5 V	-	5.8	10	-	15	Ω
		$V_I = V_{CC}$; see Figure 9						
		I_{SW} = 4 mA; V_{CC} = 1.65 V to 1.95 V	-	10.4	30	-	45	Ω
		I_{SW} = 8 mA; V_{CC} = 2.3 V to 2.7 V	-	7.6	20	-	30	Ω
		I_{SW} = 12 mA; V_{CC} = 2.7 V	-	7.0	18	-	27	Ω
		I_{SW} = 24 mA; V_{CC} = 3.0 V to 3.6 V	-	6.1	15	-	23	Ω
		I_{SW} = 32 mA; V_{CC} = 4.5 V to 5.5 V	-	4.9	10	-	15	Ω

Table 8. ON resistance *...continued*

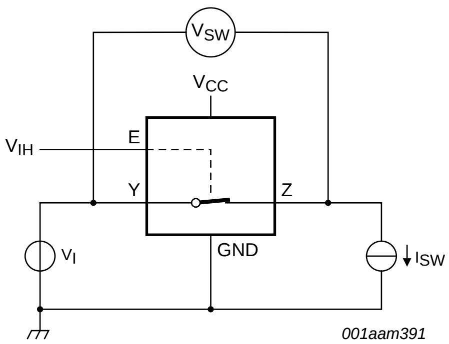
At recommended operating conditions; voltages are referenced to GND (ground 0 V); for graphs see Figure 10 to Figure 15.

Symbol	Parameter	Conditions	–40 °C to +85 °C			–40 °C to +125 °C		Unit
			Min	Typ[1]	Max	Min	Max	
$R_{ON(flat)}$	ON resistance (flatness)	V_I = GND to V_{CC} [2]						
		I_{SW} = 4 mA; V_{CC} = 1.65 V to 1.95 V	-	26.0	-	-	-	Ω
		I_{SW} = 8 mA; V_{CC} = 2.3 V to 2.7 V	-	5.0	-	-	-	Ω
		I_{SW} = 12 mA; V_{CC} = 2.7 V	-	3.5	-	-	-	Ω
		I_{SW} = 24 mA; V_{CC} = 3.0 V to 3.6 V	-	2.0	-	-	-	Ω
		I_{SW} = 32 mA; V_{CC} = 4.5 V to 5.5 V	-	1.5	-	-	-	Ω

[1] Typical values are measured at T_{amb} = 25 °C and nominal V_{CC}.

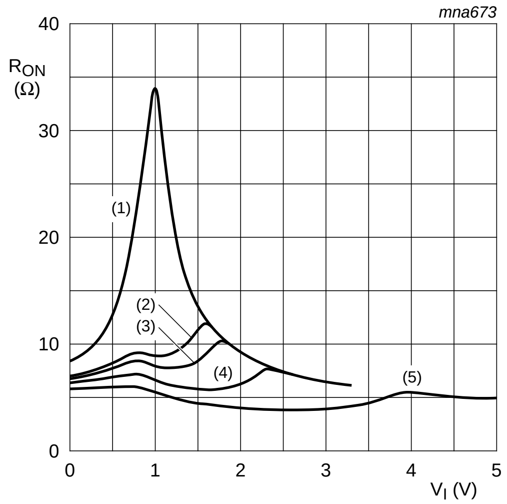
[2] Flatness is defined as the difference between the maximum and minimum value of ON resistance measured at identical V_{CC} and temperature.

10.3 ON resistance test circuit and graphs



$R_{ON} = V_{SW}/I_{SW}$.

Fig 9. Test circuit for measuring ON resistance



(1) V_{CC} = 1.8 V.

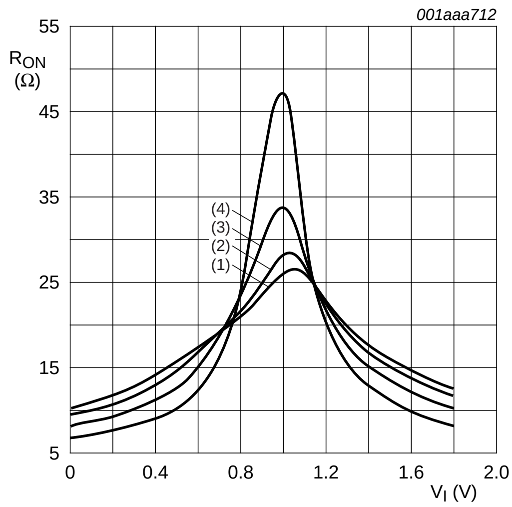
(2) V_{CC} = 2.5 V.

(3) V_{CC} = 2.7 V.

(4) V_{CC} = 3.3 V.

(5) V_{CC} = 5.0 V.

Fig 10. Typical ON resistance as a function of input voltage; T_{amb} = 25 °C



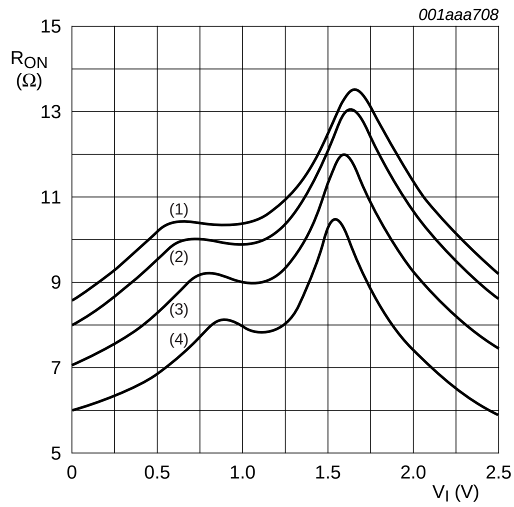
(1) T_{amb} = 125 °C.

(2) T_{amb} = 85 °C.

(3) T_{amb} = 25 °C.

(4) T_{amb} = −40 °C.

Fig 11. ON resistance as a function of input voltage; V_{CC} = 1.8 V



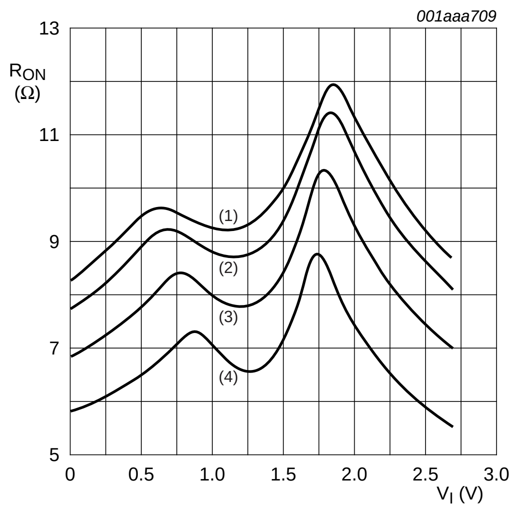
(1) T_{amb} = 125 °C.

(2) T_{amb} = 85 °C.

(3) T_{amb} = 25 °C.

(4) T_{amb} = −40 °C.

Fig 12. ON resistance as a function of input voltage; V_{CC} = 2.5 V



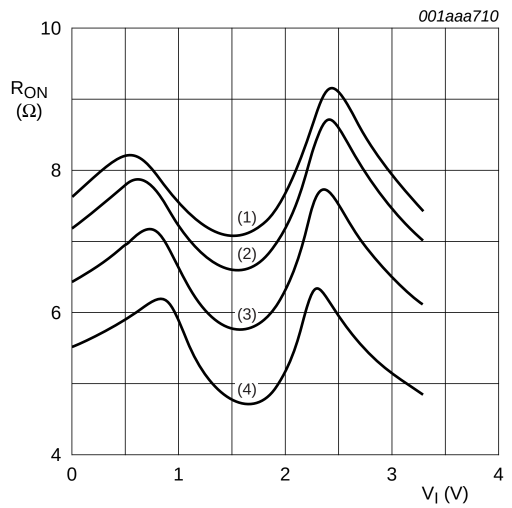
(1) T_{amb} = 125 °C.

(2) T_{amb} = 85 °C.

(3) T_{amb} = 25 °C.

(4) T_{amb} = −40 °C.

Fig 13. ON resistance as a function of input voltage; V_{CC} = 2.7 V



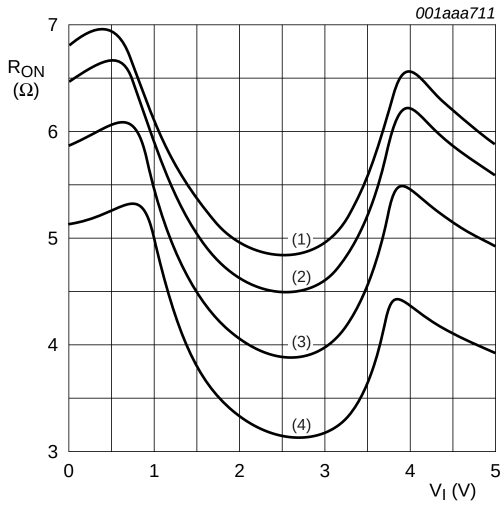
(1) T_{amb} = 125 °C.

(2) T_{amb} = 85 °C.

(3) T_{amb} = 25 °C.

(4) T_{amb} = −40 °C.

Fig 14. ON resistance as a function of input voltage; V_{CC} = 3.3 V



(1) T_{amb} = 125 °C.

(2) T_{amb} = 85 °C.

(3) T_{amb} = 25 °C.

(4) T_{amb} = −40 °C.

Fig 15. ON resistance as a function of input voltage; V_{CC} = 5.0 V

11. Dynamic characteristics

Table 9. Dynamic characteristics

At recommended operating conditions; voltages are referenced to GND (ground = 0 V); for test circuit see Figure 18.

Symbol	Parameter	Conditions		−40 °C to +85 °C			−40 °C to +125 °C		Unit
				Min	Typ[1]	Max	Min	Max	
t_{pd}	propagation delay	Y to Z or Z to Y; see Figure 16	[2][3]						
		V_{CC} = 1.65 V to 1.95 V		-	0.8	2.0	-	3.0	ns
		V_{CC} = 2.3 V to 2.7 V		-	0.4	1.2	-	2.0	ns
		V_{CC} = 2.7 V		-	0.4	1.0	-	1.5	ns
		V_{CC} = 3.0 V to 3.6 V		-	0.3	0.8	-	1.5	ns
		V_{CC} = 4.5 V to 5.5 V		-	0.2	0.6	-	1.0	ns
t_{en}	enable time	E to Y or Z; see Figure 17	[4]						
		V_{CC} = 1.65 V to 1.95 V		1.0	5.3	12	1.0	15.5	ns
		V_{CC} = 2.3 V to 2.7 V		1.0	3.0	6.5	1.0	8.5	ns
		V_{CC} = 2.7 V		1.0	2.6	6.0	1.0	8.0	ns
		V_{CC} = 3.0 V to 3.6 V		1.0	2.5	5.0	1.0	6.5	ns
		V_{CC} = 4.5 V to 5.5 V		1.0	1.9	4.2	1.0	5.5	ns

Table 9. Dynamic characteristics *...continued*

At recommended operating conditions; voltages are referenced to GND (ground = 0 V); for test circuit see Figure 18.

Symbol	Parameter	Conditions		−40 °C to +85 °C			−40 °C to +125 °C		Unit
				Min	Typ[1]	Max	Min	Max	
t_{dis}	disable time	E to Y or Z; see Figure 17	[5]						
		V_{CC} = 1.65 V to 1.95 V		1.0	4.2	10	1.0	13	ns
		V_{CC} = 2.3 V to 2.7 V		1.0	2.4	6.9	1.0	9.0	ns
		V_{CC} = 2.7 V		1.0	3.6	7.5	1.0	9.5	ns
		V_{CC} = 3.0 V to 3.6 V		1.0	3.4	6.5	1.0	8.5	ns
		V_{CC} = 4.5 V to 5.5 V		1.0	2.5	5.0	1.0	6.5	ns
C_{PD}	power dissipation capacitance	C_L = 50 pF; f_i = 10 MHz; V_I = GND to V_{CC}	[6]						
		V_{CC} = 2.5 V		-	9.8	-	-	-	pF
		V_{CC} = 3.3 V		-	12.0	-	-	-	pF
		V_{CC} = 5.0 V		-	17.3	-	-	-	pF

[1] Typical values are measured at T_{amb} = 25 °C and nominal V_{CC}.

[2] t_{pd} is the same as t_{PLH} and t_{PHL}

[3] propagation delay is the calculated RC time constant of the typical ON resistance of the switch and the specified capacitance when driven by an ideal voltage source (zero output impedance).

[4] t_{en} is the same as t_{PZH} and t_{PZL}

[5] t_{dis} is the same as t_{PLZ} and t_{PHZ}

[6] C_{PD} is used to determine the dynamic power dissipation (P_D in μW).

$P_D = C_{PD} \times V_{CC}^2 \times f_i \times N + \Sigma\{(C_L + C_{S(ON)}) \times V_{CC}^2 \times f_o\}$ where:

f_i = input frequency in MHz;

f_o = output frequency in MHz;

C_L = output load capacitance in pF;

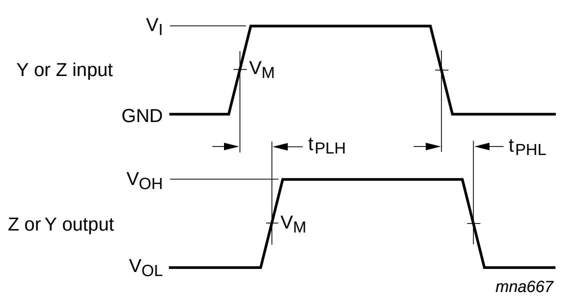
$C_{S(ON)}$ = maximum ON-state switch capacitance in pF;

V_{CC} = supply voltage in V;

N = number of inputs switching;

$\Sigma\{(C_L + C_{S(ON)}) \times V_{CC}^2 \times f_o\}$ = sum of the outputs.

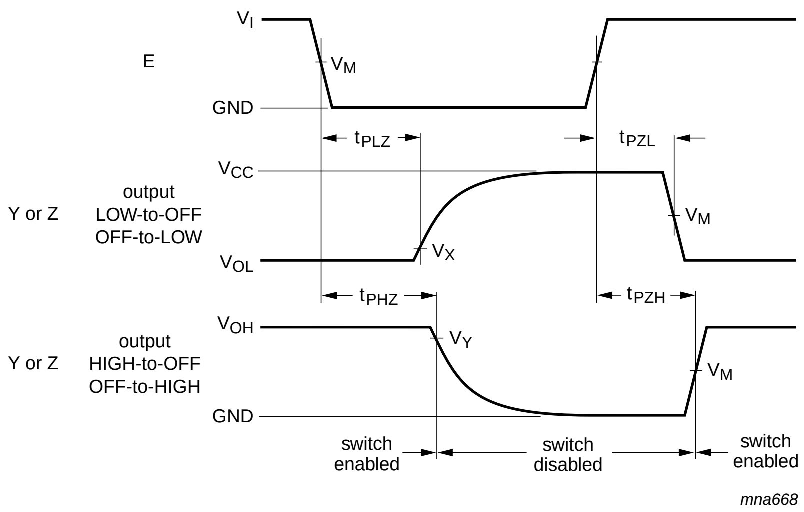
11.1 Waveforms and test circuit



Measurement points are given in Table 10.

Logic levels: V_{OL} and V_{OH} are typical output voltage levels that occur with the output load.

Fig 16. Input (Y or Z) to output (Z or Y) propagation delays



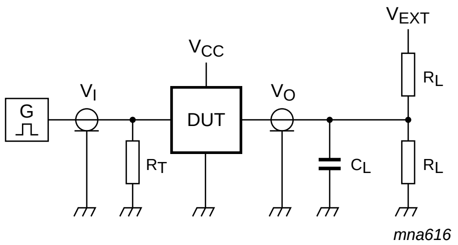
Measurement points are given in Table 10.

Logic levels: V_{OL} and V_{OH} are typical output voltage levels that occur with the output load.

Fig 17. Enable and disable times

Table 10. Measurement points

Supply voltage	Input	Output		
V_{CC}	V_M	V_M	V_X	V_Y
1.65 V to 1.95 V	$0.5V_{CC}$	$0.5V_{CC}$	V_{OL} + 0.15 V	V_{OH} − 0.15 V
2.3 V to 2.7 V	$0.5V_{CC}$	$0.5V_{CC}$	V_{OL} + 0.15 V	V_{OH} − 0.15 V
2.7 V	1.5 V	1.5 V	V_{OL} + 0.3 V	V_{OH} − 0.3 V
3.0 V to 3.6 V	1.5 V	1.5 V	V_{OL} + 0.3 V	V_{OH} − 0.3 V
4.5 V to 5.5 V	$0.5V_{CC}$	$0.5V_{CC}$	V_{OL} + 0.3 V	V_{OH} − 0.3 V



Test data is given in Table 11.

Definitions for test circuit:

R_T = Termination resistance should be equal to output impedance Z_o of the pulse generator.

C_L = Load capacitance including jig and probe capacitance.

R_L = Load resistance.

V_{EXT} = External voltage for measuring switching times.

Fig 18. Test circuit for measuring switching times

Table 11. Test data

Supply voltage	Input		Load		V_{EXT}		
V_{CC}	V_I	t_r, t_f	C_L	R_L	t_{PLH}, t_{PHL}	t_{PZH}, t_{PHZ}	t_{PZL}, t_{PLZ}
1.65 V to 1.95 V	V_{CC}	≤ 2.0 ns	30 pF	1 kΩ	open	GND	$2V_{CC}$
2.3 V to 2.7 V	V_{CC}	≤ 2.0 ns	30 pF	500 Ω	open	GND	$2V_{CC}$
2.7 V	2.7 V	≤ 2.5 ns	50 pF	500 Ω	open	GND	6 V
3.0 V to 3.6 V	2.7 V	≤ 2.5 ns	50 pF	500 Ω	open	GND	6 V
4.5 V to 5.5 V	V_{CC}	≤ 2.5 ns	50 pF	500 Ω	open	GND	$2V_{CC}$

11.2 Additional dynamic characteristics

Table 12. Additional dynamic characteristics

At recommended operating conditions; voltages are referenced to GND (ground = 0 V); T_{amb} = 25 °C.

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
THD	total harmonic distortion	R_L = 10 kΩ; C_L = 50 pF; f_i = 1 kHz; see Figure 19				
		V_{CC} = 1.65 V	-	0.032	-	%
		V_{CC} = 2.3 V	-	0.008	-	%
		V_{CC} = 3.0 V	-	0.006	-	%
		V_{CC} = 4.5 V	-	0.001	-	%
		R_L = 10 kΩ; C_L = 50 pF; f_i = 10 kHz; see Figure 19				
		V_{CC} = 1.65 V	-	0.068	-	%
		V_{CC} = 2.3 V	-	0.009	-	%
		V_{CC} = 3.0 V	-	0.008	-	%
		V_{CC} = 4.5 V	-	0.006	-	%

Table 12. Additional dynamic characteristics *...continued*

At recommended operating conditions; voltages are referenced to GND (ground = 0 V); T_{amb} = 25 °C.

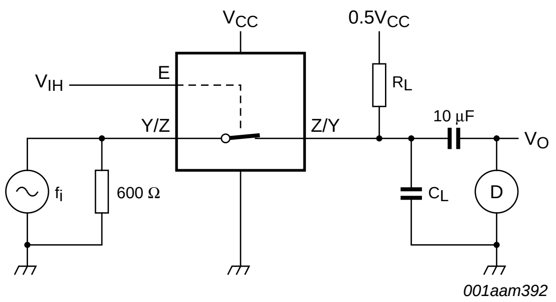
Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$f_{(-3dB)}$	–3 dB frequency response	R_L = 600 Ω; C_L = 50 pF; see Figure 20				
		V_{CC} = 1.65 V	-	135	-	MHz
		V_{CC} = 2.3 V	-	145	-	MHz
		V_{CC} = 3.0 V	-	150	-	MHz
		V_{CC} = 4.5 V	-	155	-	MHz
		R_L = 50 Ω; C_L = 5 pF; see Figure 20				
		V_{CC} = 1.65 V	-	> 500	-	MHz
		V_{CC} = 2.3 V	-	> 500	-	MHz
		V_{CC} = 3.0 V	-	> 500	-	MHz
		V_{CC} = 4.5 V	-	> 500	-	MHz
		R_L = 50 Ω; C_L = 10 pF; see Figure 20				
		V_{CC} = 1.65 V	-	200	-	MHz
		V_{CC} = 2.3 V	-	350	-	MHz
		V_{CC} = 3.0 V	-	410	-	MHz
		V_{CC} = 4.5 V	-	440	-	MHz
α_{iso}	isolation (OFF-state)	R_L = 600 Ω; C_L = 50 pF; f_i = 1 MHz; see Figure 21				
		V_{CC} = 1.65 V	-	–46	-	dB
		V_{CC} = 2.3 V	-	–46	-	dB
		V_{CC} = 3.0 V	-	–46	-	dB
		V_{CC} = 4.5 V	-	–46	-	dB
		R_L = 50 Ω; C_L = 5 pF; f_i = 1 MHz; see Figure 21				
		V_{CC} = 1.65 V	-	–37	-	dB
		V_{CC} = 2.3 V	-	–37	-	dB
		V_{CC} = 3.0 V	-	–37	-	dB
		V_{CC} = 4.5 V	-	–37	-	dB
V_{ct}	crosstalk voltage	between digital input and switch; R_L = 600 Ω; C_L = 50 pF; f_i = 1 MHz; t_r = t_f = 2 ns; see Figure 22				
		V_{CC} = 1.65 V	-	69	-	mV
		V_{CC} = 2.3 V	-	87	-	mV
		V_{CC} = 3.0 V	-	156	-	mV
		V_{CC} = 4.5 V	-	302	-	mV

Table 12. Additional dynamic characteristics *...continued*

At recommended operating conditions; voltages are referenced to GND (ground = 0 V); T_{amb} = 25 °C.

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Q_{inj}	charge injection	C_L = 0.1 nF; V_{gen} = 0 V; R_{gen} = 0 Ω; f_i = 1 MHz; R_L = 1 MΩ; see Figure 23				
		V_{CC} = 1.8 V	-	3.3	-	pC
		V_{CC} = 2.5 V	-	4.1	-	pC
		V_{CC} = 3.3 V	-	5.0	-	pC
		V_{CC} = 4.5 V	-	6.4	-	pC
		V_{CC} = 5.5 V	-	7.5	-	pC

11.3 Test circuits



Test conditions:

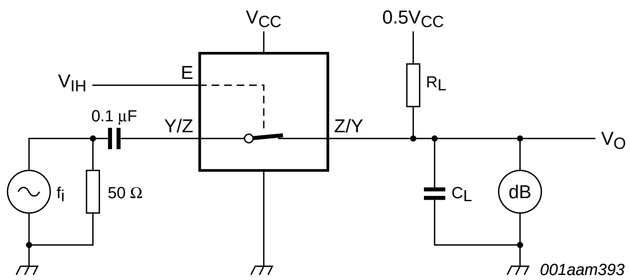
V_{CC} = 1.65 V: V_i = 1.4 V (p-p).

V_{CC} = 2.3 V: V_i = 2 V (p-p).

V_{CC} = 3 V: V_i = 2.5 V (p-p).

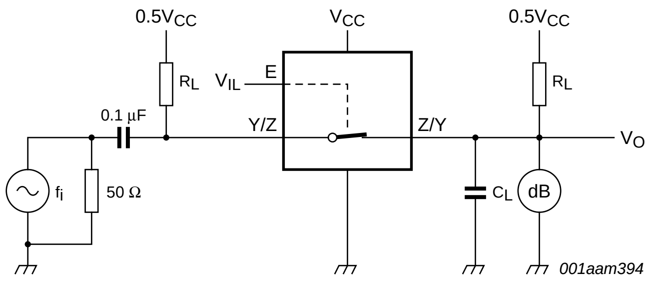
V_{CC} = 4.5 V: V_i = 4 V (p-p).

Fig 19. Test circuit for measuring total harmonic distortion



Adjust f_i voltage to obtain 0 dBm level at output. Increase f_i frequency until dB meter reads −3 dB.

Fig 20. Test circuit for measuring the frequency response when switch is in ON-state



Adjust f_i voltage to obtain 0 dBm level at input.

Fig 21. Test circuit for measuring isolation (OFF-state)

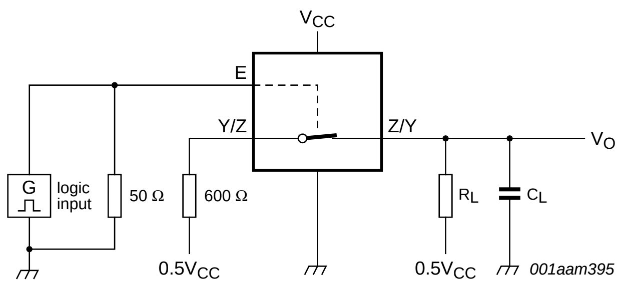
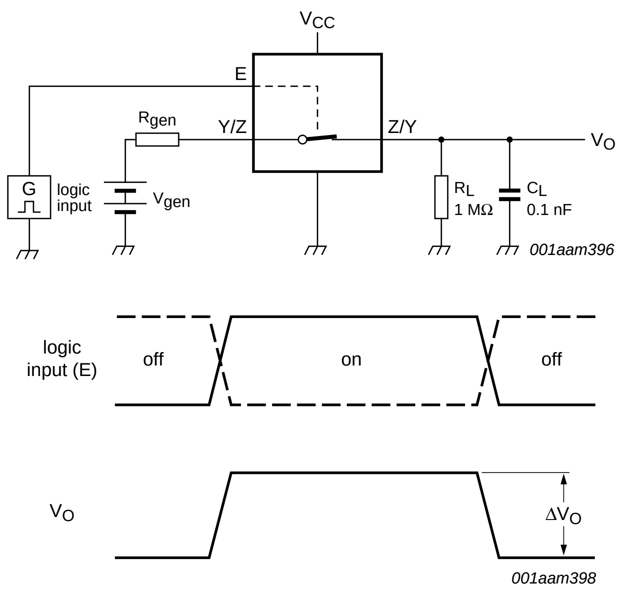


Fig 22. Test circuit for measuring crosstalk between digital input and switch



$Q_{inj} = \Delta V_O \times C_L$.

ΔV_O = output voltage variation.

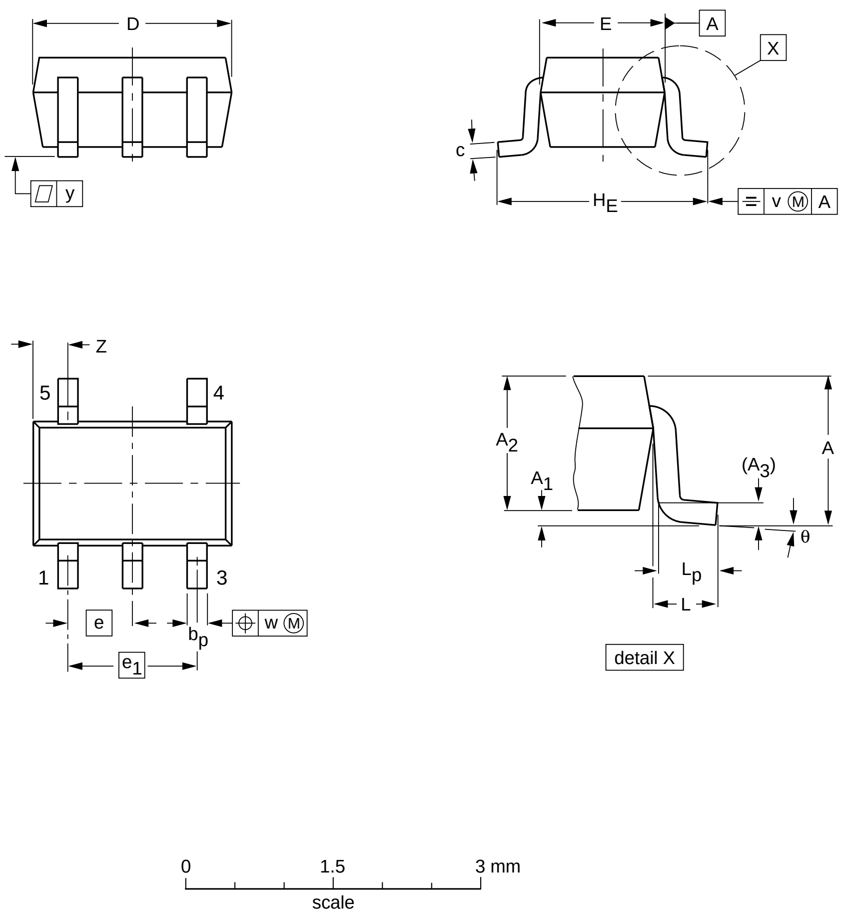
R_{gen} = generator resistance.

V_{gen} = generator voltage.

Fig 23. Test circuit for measuring charge injection

12. Package outline

TSSOP5: plastic thin shrink small outline package; 5 leads; body width 1.25 mm **SOT353-1**



DIMENSIONS (mm are the original dimensions)

UNIT	A max.	A_1	A_2	A_3	b_p	c	$D^{(1)}$	$E^{(1)}$	e	e_1	H_E	L	L_p	v	w	y	$Z^{(1)}$	θ
mm	1.1	0.1 0	1.0 0.8	0.15	0.30 0.15	0.25 0.08	2.25 1.85	1.35 1.15	0.65	1.3	2.25 2.0	0.425	0.46 0.21	0.3	0.1	0.1	0.60 0.15	7° 0°

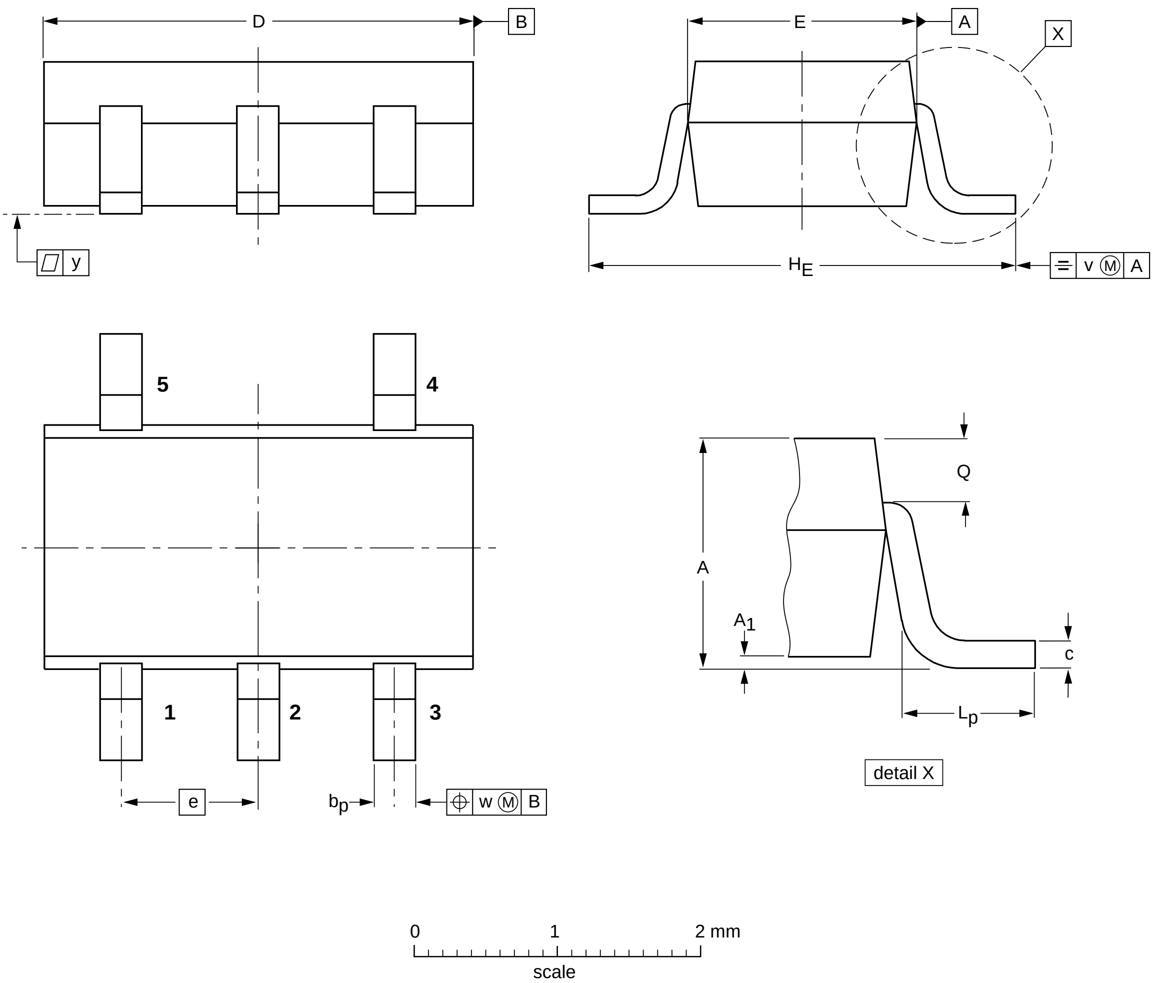
Note

1. Plastic or metal protrusions of 0.15 mm maximum per side are not included.

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA			
SOT353-1		MO-203	SC-88A			~~00-09-01~~ 03-02-19

Fig 24. Package outline SOT353-1 (TSSOP5)

Plastic surface-mounted package; 5 leads **SOT753**



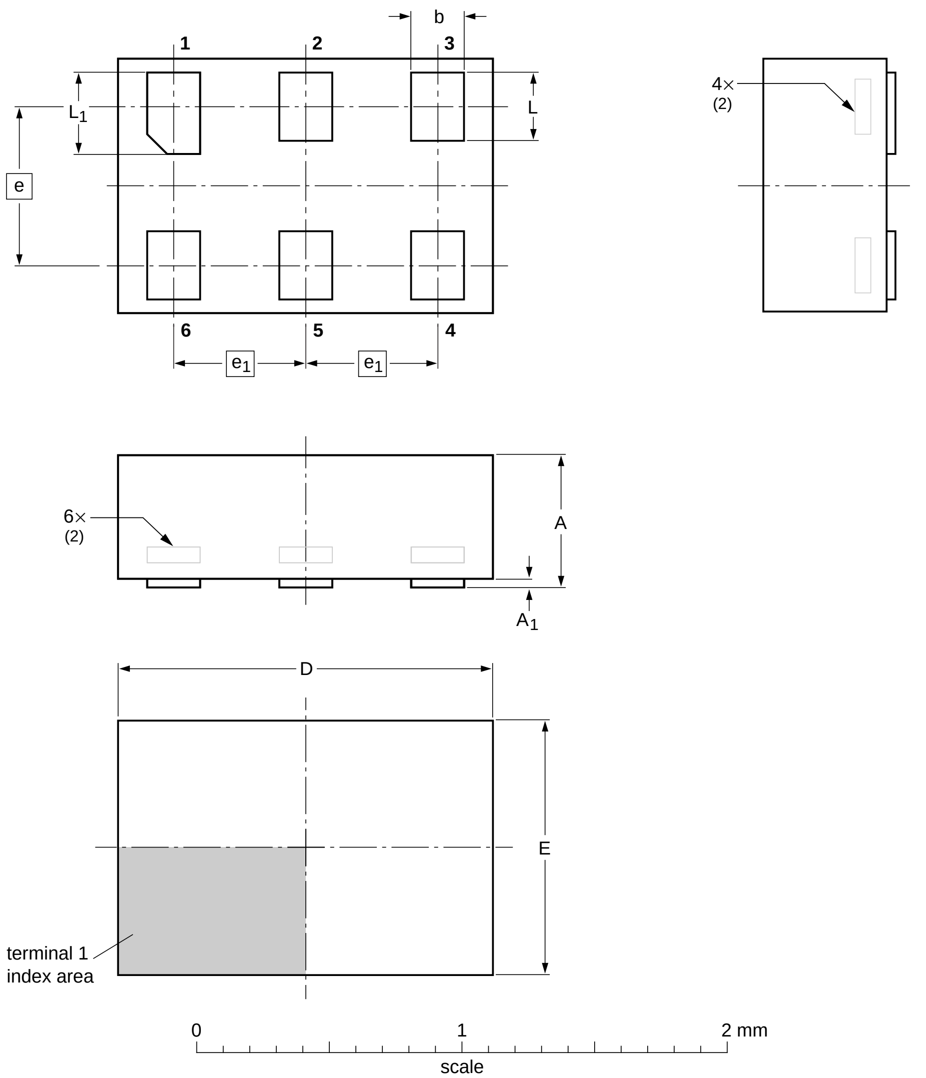
DIMENSIONS (mm are the original dimensions)

UNIT	A	A_1	b_p	c	D	E	e	H_E	L_p	Q	v	w	y
mm	1.1 0.9	0.100 0.013	0.40 0.25	0.26 0.10	3.1 2.7	1.7 1.3	0.95	3.0 2.5	0.6 0.2	0.33 0.23	0.2	0.2	0.1

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA			
SOT753			SC-74A			~~02-04-16~~ 06-03-16

Fig 25. Package outline SOT753 (SC-74A)

XSON6: plastic extremely thin small outline package; no leads; 6 terminals; body 1 x 1.45 x 0.5 mm **SOT886**



DIMENSIONS (mm are the original dimensions)

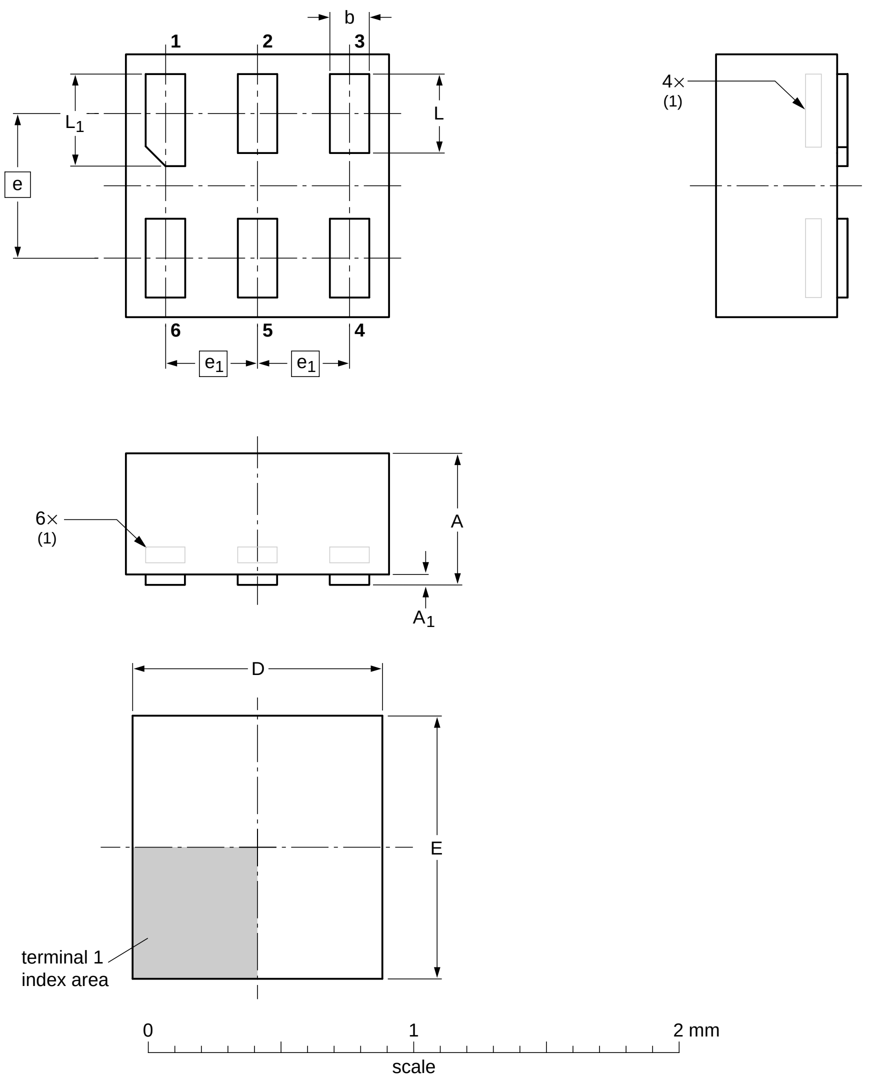
UNIT	A (1) max	A_1 max	b	D	E	e	e_1	L	L_1
mm	0.5	0.04	0.25 0.17	1.5 1.4	1.05 0.95	0.6	0.5	0.35 0.27	0.40 0.32

Notes
1. Including plating thickness.
2. Can be visible in some manufacturing processes.

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA			
SOT886		MO-252				~~04-07-15~~ 04-07-22

Fig 26. Package outline SOT886 (XSON6)

XSON6: plastic extremely thin small outline package; no leads; 6 terminals; body 1 x 1 x 0.5 mm **SOT891**



DIMENSIONS (mm are the original dimensions)

UNIT	A max	A_1 max	b	D	E	e	e_1	L	L_1
mm	0.5	0.04	0.20 0.12	1.05 0.95	1.05 0.95	0.55	0.35	0.35 0.27	0.40 0.32

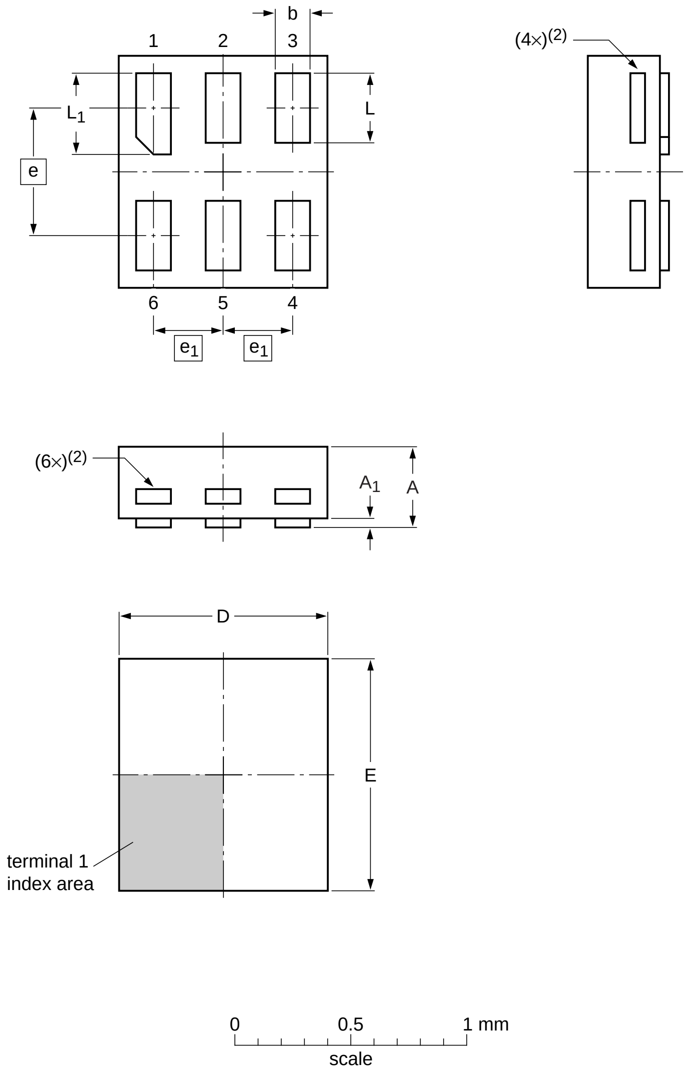
Note

1. Can be visible in some manufacturing processes.

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA			
SOT891						~~05-04-06~~ 07-05-15

Fig 27. Package outline SOT891 (XSON6)

XSON6: extremely thin small outline package; no leads;
6 terminals; body 0.9 x 1.0 x 0.35 mm **SOT1115**



Dimensions

Unit		$A^{(1)}$	A_1	b	D	E	e	e_1	L	L_1
mm	max	0.35	0.04	0.20	0.95	1.05			0.35	0.40
	nom			0.15	0.90	1.00	0.55	0.3	0.30	0.35
	min			0.12	0.85	0.95			0.27	0.32

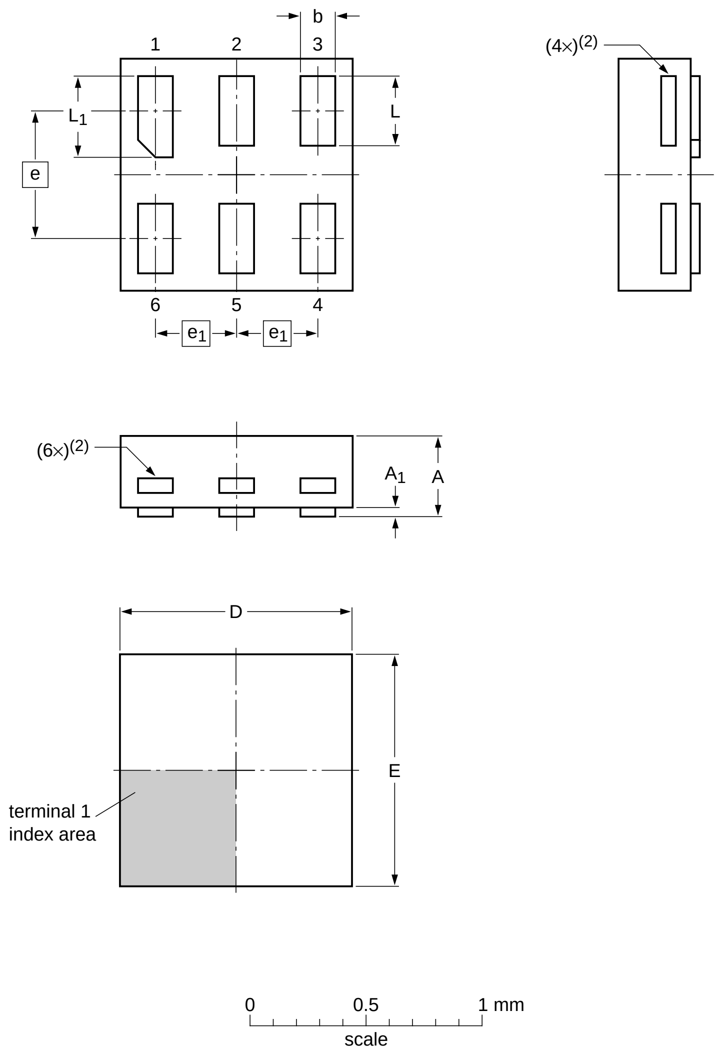
Note
1. Including plating thickness.
2. Visible depending upon used manufacturing technology.

sot1115_po

Outline version	References				European projection	Issue date
	IEC	JEDEC	JEITA			
SOT1115						~~10-04-02~~ 10-04-07

Fig 28. Package outline SOT1115 (XSON6)

XSON6: extremely thin small outline package; no leads;
6 terminals; body 1.0 x 1.0 x 0.35 mm **SOT1202**



Dimensions

Unit		A(1)	A_1	b	D	E	e	e_1	L	L_1
	max	0.35	0.04	0.20	1.05	1.05			0.35	0.40
mm	nom			0.15	1.00	1.00	0.55	0.35	0.30	0.35
	min			0.12	0.95	0.95			0.27	0.32

Note
1. Including plating thickness.
2. Visible depending upon used manufacturing technology.

sot1202_po

Outline version	References				European projection	Issue date
	IEC	JEDEC	JEITA			
SOT1202						~~10-04-02~~ 10-04-06

Fig 29. Package outline SOT1202 (XSON6)

13. Abbreviations

Table 13. Abbreviations

Acronym	Description
CMOS	Complementary Metal Oxide Semiconductor
TTL	Transistor-Transistor Logic
HBM	Human Body Model
ESD	ElectroStatic Discharge
MM	Machine Model
DUT	Device Under Test

14. Revision history

Table 14. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
74LVC1G66 v.8	20111202	Product data sheet	-	74LVC1G66 v.7
Modifications:	• Legal pages updated.			
74LVC1G66 v.7	20100730	Product data sheet	-	74LVC1G66 v.6
74LVC1G66 v.6	20070827	Product data sheet	-	74LVC1G66 v.5
74LVC1G66 v.5	20070807	Product data sheet	-	74LVC1G66 v.4
74LVC1G66 v.4	20040413	Product specification	-	74LVC1G66 v.3
74LVC1G66 v.3	20021115	Product specification	-	74LVC1G66 v.2
74LVC1G66 v.2	20020529	Product specification	-	74LVC1G66 v.1
74LVC1G66 v.1	20011030	Product specification	-	-

15. Legal information

15.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

[3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL http://www.nxp.com.

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17. Contents

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